INTEGRATED CIRCUIT **TOSHIBA** TECHNICAL DATA

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT

TA8210AH, TA8210AL

SILICON MONOLITHIC

20W BTL×2CH AUDIO POWER AMPLIFIER

The thermal resistance θ j-T of TA8210AH, TA8210AL package designed for low thermal resistance, has a high efficiency of heat radiation.

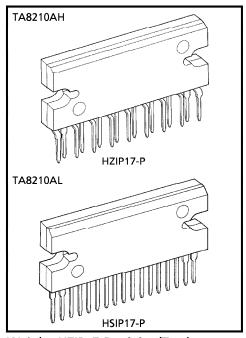
The temperature rise of chip can be reduced, and the influence from the degradation of the features due to the temperature rise at the high output can also be reduced.

This stereo audio power IC, designed for car audio use, has two built-in channels to reduce the characteristic difference between L and R channels.

In addition, the functions of stand-by and muting, and a variety of protection circuits are involved.

FEATURES

- Low Thermal Resistance : θ j-T = 1.5°C/W (Infinite Heat Sink)
- High Power
 - : POUT (1) = 22W (Typ.) / Channel $(V_{CC} = 14.4V, f = 1kHz, THD = 10\%, R_L = 4\Omega)$ POUT (2) = 19W (Typ.) / Channel $(V_{CC} = 13.2V, f = 1kHz, THD = 10\%, R_L = 4\Omega)$



Weight HZIP17-P: 9.8g (Typ.) HSIP17-P: 9.8g (Typ.)

- Low Distortion Ratio : THD = 0.04% (Typ.) (V_{CC} = 13.2V, f = 1kHz, P_{OUT} = 1W, R_L = 4 Ω , G_V = 50dB)
- Low Noise : $V_{NO} = 0.30 \text{mV}_{rms}$ (Typ.) ($V_{CC} = 13.2 \text{V}$, $R_L = 4 \Omega$, $G_V = 50 \text{dB}$, $R_q = 0 \Omega$, $BW = 20 \text{Hz} \sim 20 \text{kHz}$)
- Built-in Stand-by Function (With pin @ set a LOW, power is turned OFF.) : $I_{SB} = 1 \mu A$ (Typ.)
- Built-in Muting Function (With pin1) set at LOW, power is turned OFF.) : V (Mute) = 1V (Typ.)
- **Built-in Various Protection Circuits** Protection circuits: Thermal Shut Down, over voltage, out→V_{CC} short, out→GND short and OUT-OUT Short.
- Operating Supply Voltage : $V_{CC} = 9 \sim 18V$

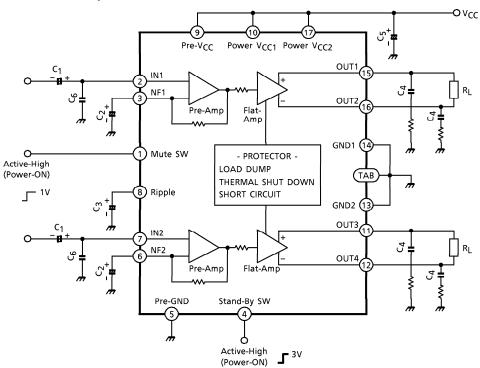
The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others. These TOSHIBA products are intended for use in general commercial applications (office equipment, communication equipment, measuring equipment, domestic appliances, etc.), please make sure that you consult with us before you use these TOSHIBA products in equipment which requires extraordinarily high quality and/or reliability, and in equipment which may involve the threatening or critical application, including by not limited to such uses as atomic energy control, airplane or spaceship instrumentation, traffic signals, medical instrumentation, combustion control, all types of safety devices, etc. TOSHIBA cannot accept and hereby discalaims liability for any damage which may occur in case the TOSHIBA products are used in such equipment or applications without prior consultation with TOSHIBA.

TA8210AH – 1 1996 - 6 - 17

TECHNICAL DATA

BLOCK DIAGRAM

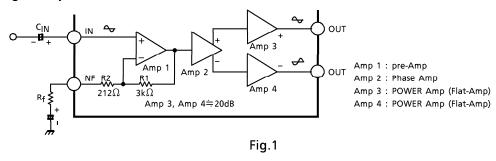
TA8210AH, TA8210AL ($G_V = 50dB$)



CAUTIONS AND APPLICATION METHOD

(Description is made only on the single channel.)

1. Voltage gain adjustment



This IC has the amplifier construction as shown in Fig.1. The Pre-Amp (Amp 1) is provided to the primary stage, and the input voltage is amplified by the Flat Amps, Amp 3 and Amp 4 of each channel through the phase Amp (Amp 2).

Since the input offset is prevented by Pre-Amp when V_{CC} is set to ON, this circuit can remarkably reduce the pop noise.

TA8210AH – 2
1996 – 6 – 17
TOSHIBA CORPORATION

The total closed loop gain G_V of this IC can be obtained by expression below when the closed loop voltage gain of Amp 1 is G_{V1} .

$$G_{V1} = 20 log \frac{R1 + (R_f + R2)}{R_f + R2}$$
 (dB) (1)

The closed loop voltage gain of POWER Amp, Amp 3 and Amp 4 is fixed at $G_{V3} = G_{V4} = 20$ dB.

Therefore, the total closed circuit voltage gain G_V is obtained through BTL connection by the expression below.

For example, when $R_f = 0\Omega$, G_V is obtained by the expressions (1) and (2) as shown below.

$$G_V = 24 + 20 + 6 = 50dB$$

The voltage gain is reduced when $R_{\mbox{f}}$ is increased. (Fig.2) With the voltage gain reduced, since (1) the oscillation stability is reduced, and (2) the pop noise changes when $V_{\mbox{CC}}$ is set to ON, refer to the items 3 and 4.

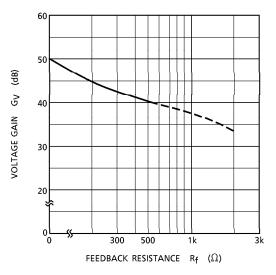


Fig.2

2. Stand-by SW function

By means of controlling pin (Stand-by terminal) to High and Low, the power supply can be set to ON and OFF. The threshold voltage of pin (is set at 2.1V (3VBE), and the Power Supply current is about 1μ A (Typ.) at the stand-by state.

Pin 4 control voltage: V (SB)

STAND-BY	POWER	V (SB) (V)
ON	OFF	0~2
OFF	ON	3~VCC

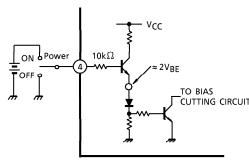


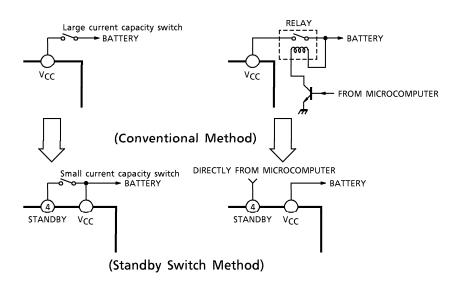
Fig.3 With pin 4 set to High, Power is turned ON.

Advantage of stand-by SW

- (1) Since V_{CC} can directly be controlled to ON/OFF by the microcomputer, the switching relay can be omitted.
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching.

TA8210AH – 3
1996 – 6 – 17
TOSHIBA CORPORATION

TECHNICAL DATA



3. Preventive measure against oscillation

For preventing the oscillation, it is advisable to use C₄, the condenser of polyester film having small characteristic fluctuation of the temperature and the frequency.

The resistance R to be series applied to C₄ is effective for phase correction of high frequency, and improves the oscillation allowance.

Since the oscillation allowance is varied according to the causes described below, perform the temperature test to check the oscillation allowance.

- (1) Voltage gain to be used (G_V Setting)
- (2) Capacity value of condenser
- (3) Kind of condenser
- (4) Layout of printed board

In case of its use with the voltage gain G_V reduced or with the feedback amount increased, care must be taken because the phase-inversion is caused by the high frequency resulting in making the oscillation viably generated.

4. Input offset prevention circuit at V_{CC}→ON

Having the Pre-Amp (Amp 1) mounted on the primary stage, this IC contains the circuit for making the Amp 1 input voltage and the NF terminal voltage equipotential.

Therefore, the offset voltage produced at the input stage is suppressed to prevent the pop noise at $V_{CC}\rightarrow ON$. The capacity values of the input and NF condenser (C_1 and C_2) shall be set according to the gain to be used.

(Reference) (A) At
$$G_V = 50 dB$$
 ($R_f = 0 \Omega$)
 $C_1 = 4.7 \mu F$, $C_2 = 47 \mu F$
(B) At $G_V = 40 dB$ ($R_f = 470 \Omega$)
 $C_1 = 3.3 \mu F$, $C_2 = 33 \mu F$

TA8210AH – 4
1996 – 6 – 17
TOSHIBA CORPORATION

TA8210AH, TA8210AL

TECHNICAL DATA

5. Muting function

Through setting pin① (mute terminal) at about 1V or less, muting becomes possible.

The interval circuit of IC is shown in Fig.4.

When pin① is set to LOW, Q1 and Q2 are turned to ON, the charge of the ripple condenser is discharged and the bias is cut. The mute amount of 60dB or over can be obtained.

Since this muting function rapidly discharge the charge of the ripple filter capacitor of pin®, the pop noise is generated by the DC fluctuation of the bias section.

Therefore, this muting function is not appropriate to the audio muting but it is effective in muting at $V_{CC}\rightarrow ON$.

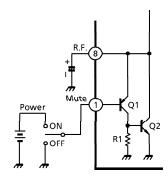


Fig.4 Mute circuit

6. External part list and description

C)/D4	RECOM-		INFLU		
SYM- BOL	MENDED VALUE	FEATURE	SMALLER THAN RECOMMENDED VALUE	LARGER THAN RECOMMENDED VALUE	REMARKS
c ₁	4.7 μ F	DC blocking	Related to non hoise at VCC→UN		Related to gain. Refer to item 4.
			Related to pop noise at	: V _{CC} →ON.	
		Feedback	Determination of low co	ut-off frequency.	
C ₂	47 μF	condenser	$C_2 = \frac{1}{2\pi \cdot f_L \cdot R_f}$		
C ₃	220 μF	Ripple	Time constant is small	Time constant is large	
-3	220μ1	reduction	at V _{CC} →ON or OFF.	at V _{CC} →ON or OFF.	
c ₄	0.12 μF	Oscillation prevention	Made liable to oscillate.	Oscillation allowance.	Refer to item 3.
			For filtering power supply hum and ripple.		
C ₅	1000µF	Ripple filter	Large at using AC rectified power supply.		
			Small at using DC powe		
Ca	1000pE	Oscillation	Oscillation allowance improved.		Refer to item 3.
C ₆ 1000pF		prevention	Noise Reduction		Refer to item 3.

TA8210AH – 5
<u> 1996 – 6 – 17</u>
TOSHIBA CORPORATION

TECHNICAL DATA

TA8210AH, TA8210AL

MAXIMUM RATINGS (Ta = 25° C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Supply Voltage (0.2s)	V _{CC} (surge)	50	V
DC Supply Voltage	VCC (DC)	25	V
Operating Supply Voltage	V _{CC (opr)}	18	V
Output Current (Peak)	I _{O (peak)}	9	Α
Power Dissipation	PD	50	W
Operating Temperature	T _{opr}	- 30∼85	°C
Storage Temperature	T _{stg}	- 55∼150	°C

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, $V_{CC} = 13.2V$, $R_L = 4\Omega$, f = 1kHz, $Ta = 25^{\circ}C$)

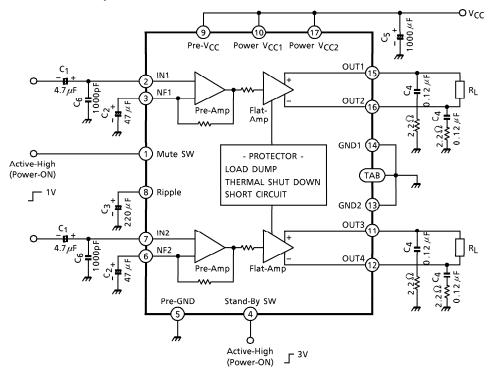
CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Quiescent Supply Current	lccq	—	V _{IN} = 0		120	250	mA	
Outrot Bassan	POUT (1)	—	V _{CC} = 14.4V, THD = 10%	_	22	_	\^/	
Output Power	POUT (2)	_	THD = 10%	16	19	_	⊣ w	
Total Harmonic Distortion Ratio	THD		P _{OUT} = 1W	_	0.04	0.4	%	
Voltage Gain	GV	_	_	48	50	52	dB	
Output Noise Voltage	V _{NO}	_	$R_g = 0\Omega$, BW = 20Hz~20kHz		0.30	0.70	mV _{rms}	
Ripple Rejection Ratio	R.R.		fripple = 100 Hz, R _g = 600Ω	40	54	_	dB	
Input Resistance	R _{IN}	_	_	_	30	_	kΩ	
Output Offset Voltage	Voffset	_	V _{IN} = 0	- 0.3	0	0.3	mV	
Current at Stand-by State	I _{SB}	_	_	_	1	10	μA	
Cross Talk	C.T.	_	$R_g = 600\Omega$, $V_{OUT} = 0.775V_{rms}$ (0dBm)	_	60	_	dB	
Pin Control Voltage	V _{SB}	_	Stand-by→OFF (Power→ON)	2.5	_	V _C C	V	
Pin① Control Voltage	V (Mute)	_	Mute→ON (Power→OFF)		1.0	2.0	V	

TA8210AH – 6	
1996 – 6 – 17	
· ·	

TECHNICAL DATA

TEST CIRCUIT

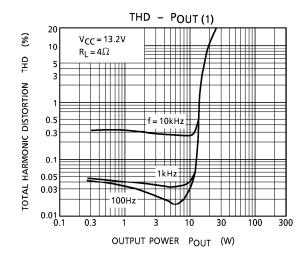
TA8210AH, TA8210AL $(G_V = 50dB)$

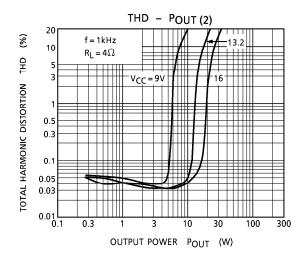


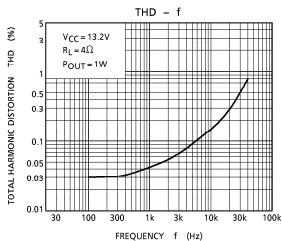
TA8210AH – 7	
1996 – 6 – 17	

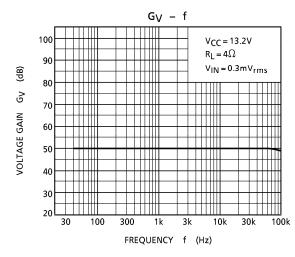
TECHNICAL DATA

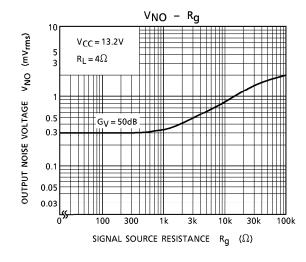
TA8210AH, TA8210AL

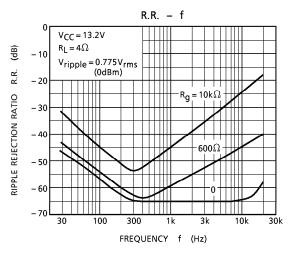








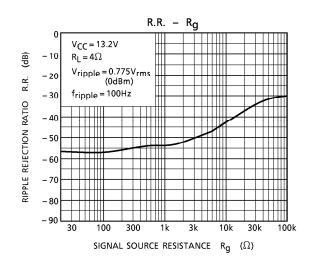


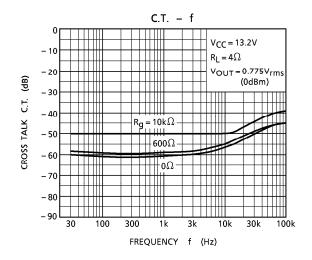


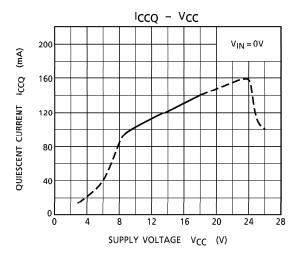
TA8210AH – 8
1996 – 6 – 17
TOSHIBA CORPORATION

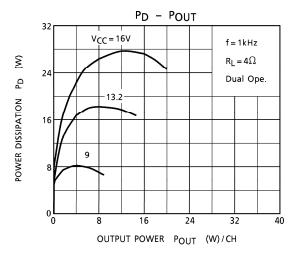
TECHNICAL DATA

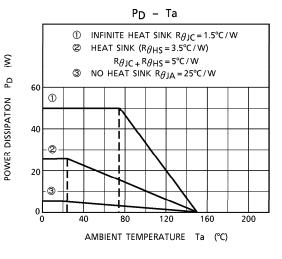
TA8210AH, TA8210AL

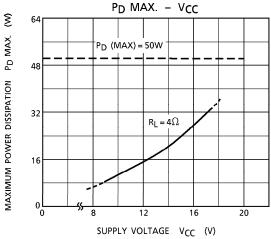












TA8210AH - 9 1996 - 6 - 17 TOSHIBA CORPORATION

INTEGRATED CIRCUIT

TOSHIBA

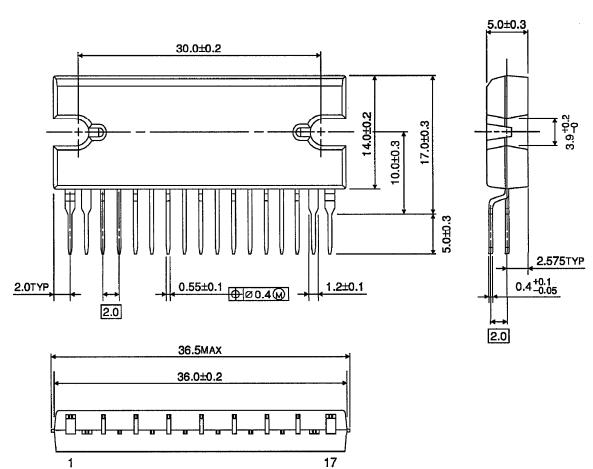
TECHNICAL DATA

TA8210AH, TA8210AL

Unit: mm

OUTLINE DRAWING

HZIP17-P

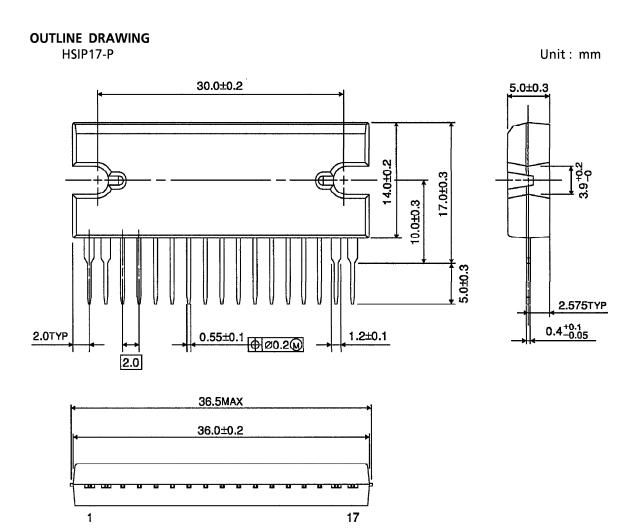


Weight: 9.8g (Typ.)

TA8210AH - 10	
1996 – 6 – 17	

TA8210AH, TA8210AL

TECHNICAL DATA



Weight: 9.8g (Typ.)

TA8210AH - 11*

1996 - 6 - 17

TOSHIBA CORPORATION